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Details

Product Status	Active
Core Processor	ARM® Cortex®-M0+
Core Size	32-Bit Single-Core
Speed	48MHz
Connectivity	I ² C, SPI, UART/USART, USB
Peripherals	DMA, I ² S, LVD, POR, PWM, WDT
Number of I/O	23
Program Memory Size	256KB (256K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	32K x 8
Voltage - Supply (Vcc/Vdd)	1.71V ~ 3.6V
Data Converters	A/D 16x16b; D/A 1x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	32-UQFN Exposed Pad
Supplier Device Package	32-QFN (5x5)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mkl27z256vm4

Table 7. Voltage and current operating behaviors (continued)

Symbol	Description	Min.	Max.	Unit	Notes
	<ul style="list-style-type: none"> $2.7\text{ V} \leq V_{DD} \leq 3.6\text{ V}$, $I_{OL} = 5\text{ mA}$ $1.71\text{ V} \leq V_{DD} \leq 2.7\text{ V}$, $I_{OL} = 1.5\text{ mA}$ 	—	0.5	V	
V_{OL}	Output low voltage — high drive pad <ul style="list-style-type: none"> $2.7\text{ V} \leq V_{DD} \leq 3.6\text{ V}$, $I_{OL} = 18\text{ mA}$ $1.71\text{ V} \leq V_{DD} \leq 2.7\text{ V}$, $I_{OL} = 6\text{ mA}$ 	— —	0.5 0.5	V V	1
I_{OLT}	Output low current total for all ports	—	100	mA	
I_{IN}	Input leakage current (per pin) for full temperature range	—	1	μA	2
I_{IN}	Input leakage current (per pin) at 25 °C	—	0.025	μA	2
I_{IN}	Input leakage current (total all pins) for full temperature range	—	64	μA	2
I_{OZ}	Hi-Z (off-state) leakage current (per pin)	—	1	μA	
R_{PU}	Internal pullup resistors	20	50	k Ω	3

- PTB0, PTB1, PTC3, PTC4, PTD6, and PTD7 I/O have both high drive and normal drive capability selected by the associated PTx_PCRn[DSE] control bit. All other GPIOs are normal drive only.
- Measured at $V_{DD} = 3.6\text{ V}$
- Measured at V_{DD} supply voltage = V_{DD} min and $V_{input} = V_{SS}$

2.2.4 Power mode transition operating behaviors

All specifications except t_{POR} and $VLLSx \rightarrow \text{RUN}$ recovery times in the following table assume this clock configuration:

- CPU and system clocks = 48 MHz
- Bus and flash clock = 24 MHz
- HIRC clock mode

Table 8. Power mode transition operating behaviors

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
t_{POR}	After a POR event, amount of time from the point V_{DD} reaches 1.8 V to execution of the first instruction across the operating temperature range of the chip.	—	—	300	μs	1
	<ul style="list-style-type: none"> $VLLS0 \rightarrow \text{RUN}$ 	—	152	166	μs	
	<ul style="list-style-type: none"> $VLLS1 \rightarrow \text{RUN}$ 	—	152	166	μs	
	<ul style="list-style-type: none"> $VLLS3 \rightarrow \text{RUN}$ 	—	93	104	μs	

Table continues on the next page...

Table 9. Power consumption operating behaviors (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
	<ul style="list-style-type: none"> at 50 °C at 85 °C at 105 °C 	—	10.26	17.62	μA	
I _{DD_LLS}	Low-leakage stop mode current, all peripheral disable, at 3.0 V <ul style="list-style-type: none"> at 25 °C and below at 50 °C at 70 °C at 85 °C at 105 °C 	—	2.06	3.33	μA	
		—	4.72	6.85		
		—	8.13	13.30		
		—	13.34	24.70		
		—	41.08	52.43		
I _{DD_LLS}	Low-leakage stop mode current with RTC current, at 3.0 V <ul style="list-style-type: none"> at 25 °C and below at 50 °C at 70 °C at 85 °C at 105 °C 	—	2.46	3.73	μA	
		—	5.12	7.25		
		—	8.53	11.78		
		—	13.74	18.91		
		—	41.48	52.83		
I _{DD_LLS}	Low-leakage stop mode current with RTC current, at 1.8 V <ul style="list-style-type: none"> at 25 °C and below at 50 °C at 70 °C at 85 °C at 105 °C 	—	2.35	2.70	μA	3
		—	4.91	6.75		
		—	8.32	11.78		
		—	13.44	18.21		
		—	40.47	51.85		
I _{DD_VLLS3}	Very-low-leakage stop mode 3 current, all peripheral disable, at 3.0 V <ul style="list-style-type: none"> at 25 °C and below at 50 °C at 70 °C at 85 °C at 105 °C 	—	1.45	1.85	μA	
		—	3.37	4.39		
		—	5.76	8.48		
		—	9.72	14.30		
		—	30.41	37.50		
I _{DD_VLLS3}	Very-low-leakage stop mode 3 current with RTC current, at 3.0 V <ul style="list-style-type: none"> at 25 °C and below at 50 °C at 70 °C at 85 °C at 105 °C 	—	2.05	2.45	μA	3
		—	3.97	4.99		
		—	6.36	9.08		
		—	10.32	14.73		
		—	31.01	38.10		

Table continues on the next page...

Table 9. Power consumption operating behaviors

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
	<ul style="list-style-type: none"> at 25 °C and below at 50 °C at 70 °C at 85 °C at 105 °C 	—	0.18	0.28	μA	
		—	1.09	1.31		
		—	2.25	2.94		
		—	4.25	5.10		
		—	15.95	19.10		

1. The analog supply current is the sum of the active or disabled current for each of the analog modules on the device. See each module's specification for its supply current.
2. MCG_Lite configured for HIRC mode. CoreMark benchmark compiled using IAR 7.10 with optimization level high, optimized for balanced.
3. RTC uses external 32 kHz crystal as clock source, and the current includes ERCLK32K power consumption.

Table 10. Low power mode peripheral adders — typical value

Symbol	Description	Temperature (°C)						Unit
		-40	25	50	70	85	105	
I _{IRC8MHz}	8 MHz internal reference clock (IRC) adder. Measured by entering STOP or VLPS mode with 8 MHz IRC enabled, MCG_SC[FCRDIV]=000b, MCG_MC[LIRC_DIV2]=000b.	93	93	93	93	93	93	μA
I _{IRC2MHz}	2 MHz internal reference clock (IRC) adder. Measured by entering STOP mode with the 2 MHz IRC enabled, MCG_SC[FCRDIV]=000b, MCG_MC[LIRC_DIV2]=000b.	29	29	29	29	29	29	μA
I _{EREFSTEN4MHz}	External 4 MHz crystal clock adder. Measured by entering STOP or VLPS mode with the crystal enabled.	206	224	230	238	245	253	μA
I _{EREFSTEN32KHz}	External 32 kHz crystal clock adder by means of the OSC0_CR[EREFSTEN and EREFSTEN] bits. Measured by entering all modes with the crystal enabled. <ul style="list-style-type: none"> VLLS1 VLLS3 LLS VLPS STOP 							nA
		440	490	540	560	570	580	
		440	490	540	560	570	580	
		490	490	540	560	570	680	
		510	560	560	560	610	680	
		510	560	560	560	610	680	
I _{LPTMR}	LPTMR peripheral adder measured by placing the device in VLLS1 mode with LPTMR enabled using LPO.	30	30	30	85	100	200	

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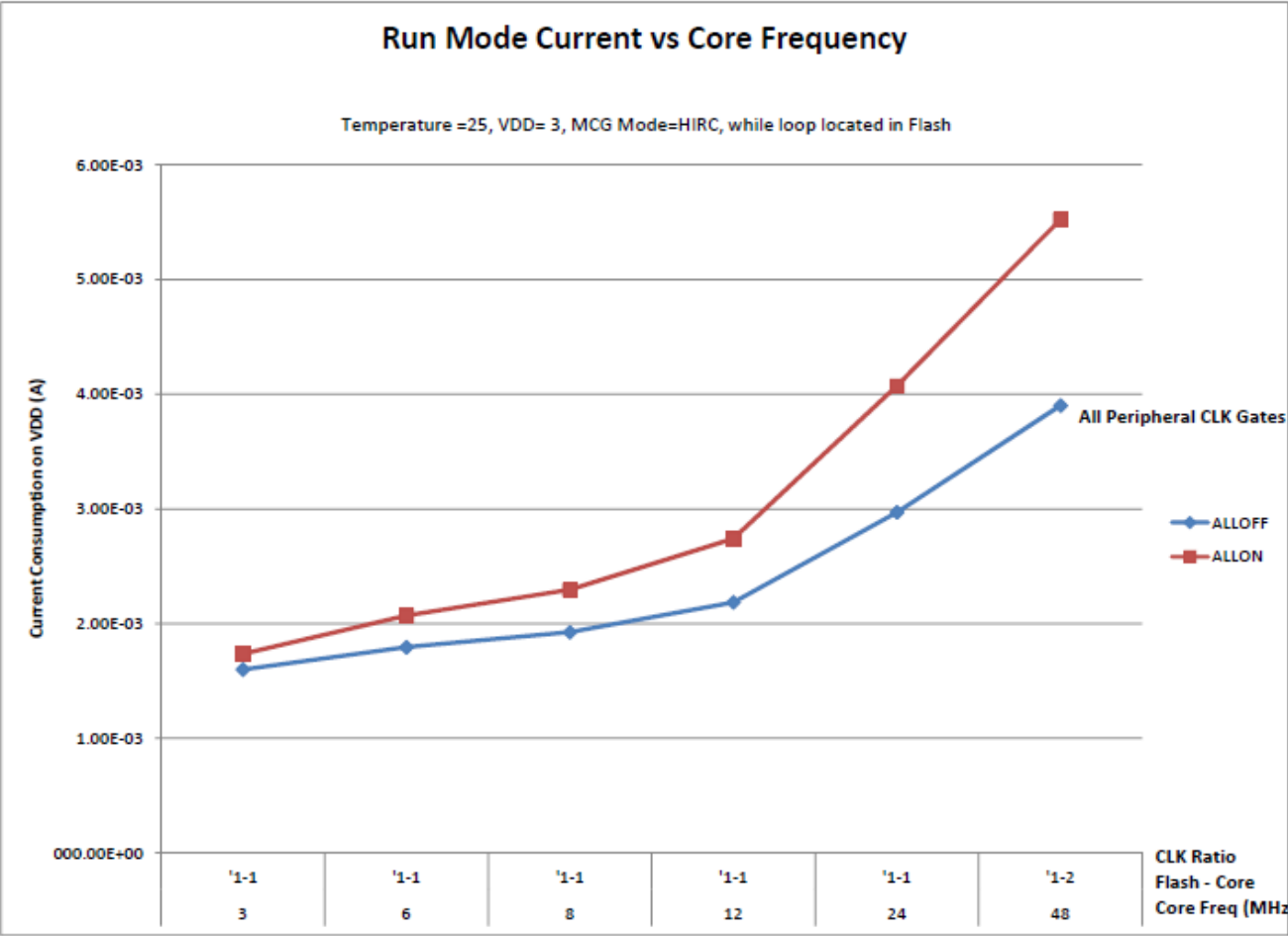


Figure 2. Run mode supply current vs. core frequency

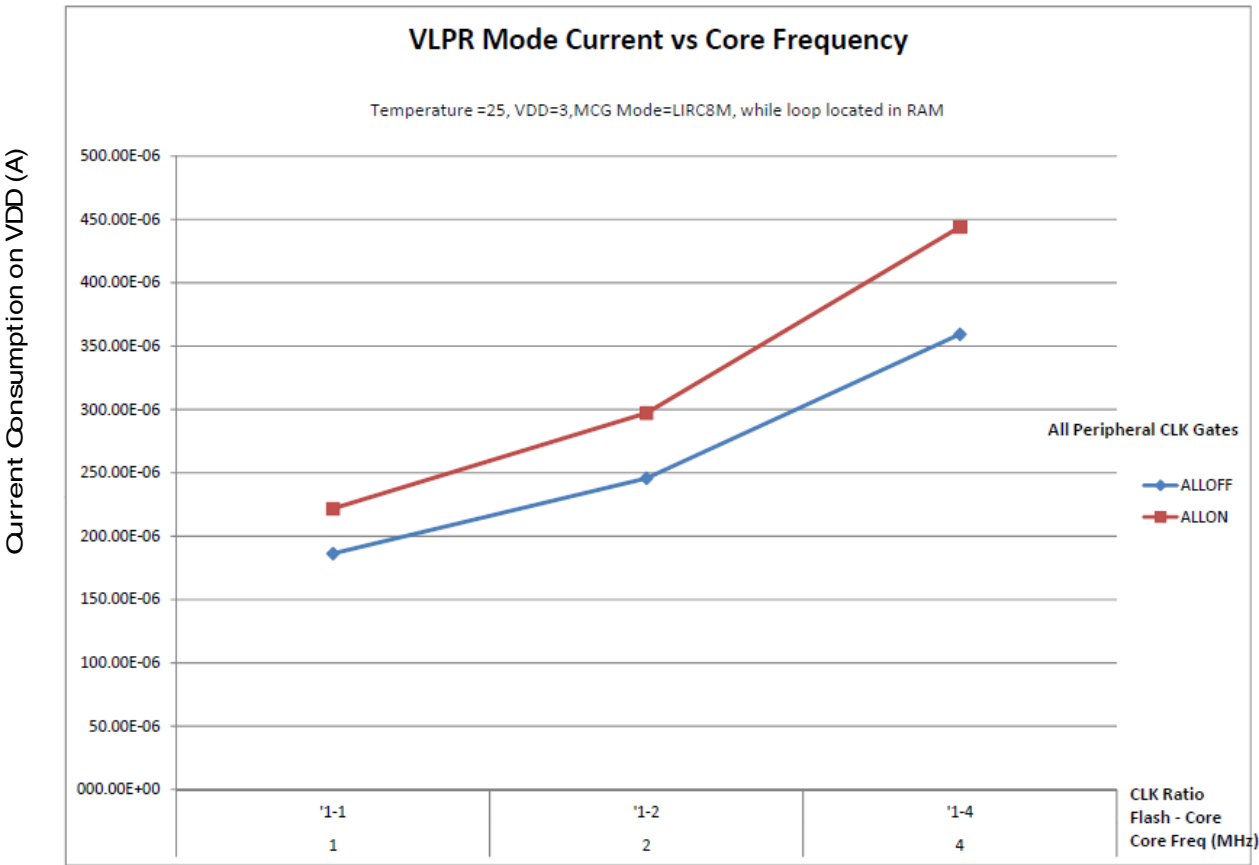


Figure 3. VLPR mode current vs. core frequency

2.2.6 EMC radiated emissions operating behaviors

Table 11. EMC radiated emissions operating behaviors for 64-pin LQFP package

Symbol	Description	Frequency band (MHz)	Typ.	Unit	Notes
V _{RE1}	Radiated emissions voltage, band 1	0.15–50	11	dBμV	1, 2
V _{RE2}	Radiated emissions voltage, band 2	50–150	12	dBμV	
V _{RE3}	Radiated emissions voltage, band 3	150–500	10	dBμV	
V _{RE4}	Radiated emissions voltage, band 4	500–1000	6	dBμV	
V _{RE_IEC}	IEC level	0.15–1000	N	—	2, 3

1. Determined according to IEC Standard 61967-1, *Integrated Circuits - Measurement of Electromagnetic Emissions, 150 kHz to 1 GHz Part 1: General Conditions and Definitions* and IEC Standard 61967-2, *Integrated Circuits - Measurement*

of Electromagnetic Emissions, 150 kHz to 1 GHz Part 2: Measurement of Radiated Emissions—TEM Cell and Wideband TEM Cell Method. Measurements were made while the microcontroller was running basic application code. The reported emission level is the value of the maximum measured emission, rounded up to the next whole number, from among the measured orientations in each frequency range.

2. $V_{DD} = 3.3\text{ V}$, $T_A = 25\text{ °C}$, $f_{OSC} = \text{IRC48M}$, $f_{SYS} = 48\text{ MHz}$, $f_{BUS} = 24\text{ MHz}$
3. Specified according to Annex D of IEC Standard 61967-2, *Measurement of Radiated Emissions—TEM Cell and Wideband TEM Cell Method*

2.2.7 Designing with radiated emissions in mind

To find application notes that provide guidance on designing your system to minimize interference from radiated emissions:

1. Go to www.freescale.com.
2. Perform a keyword search for “EMC design.”

2.2.8 Capacitance attributes

Table 12. Capacitance attributes

Symbol	Description	Min.	Max.	Unit
C_{IN}	Input capacitance	—	7	pF

2.3 Switching specifications

2.3.1 Device clock specifications

Table 13. Device clock specifications

Symbol	Description	Min.	Max.	Unit
Normal run mode				
f_{SYS}	System and core clock ¹	—	48	MHz
f_{BUS}	Bus clock ¹	—	24	MHz
f_{FLASH}	Flash clock ¹	—	24	MHz
f_{SYS_USB}	System and core clock when Full Speed USB in operation	20	—	MHz
f_{LPTMR}	LPTMR clock	—	24	MHz
VLPR and VLPS modes ²				
f_{SYS}	System and core clock	—	4	MHz
f_{BUS}	Bus clock	—	1	MHz
f_{FLASH}	Flash clock	—	1	MHz

Table continues on the next page...

Peripheral operating requirements and behaviors

4. Determined according to JEDEC Standard JESD51-2, *Integrated Circuits Thermal Test Method Environmental Conditions—Natural Convection (Still Air)*.
5. Thermal characterization parameter indicating the temperature difference between package bottom center and the junction temperature per JEDEC JESD51-12. When Greek letters are not available, the thermal characterization parameter is written as Psi-JB.

3 Peripheral operating requirements and behaviors

3.1 Core modules

3.1.1 SWD electricals

Table 17. SWD full voltage range electricals

Symbol	Description	Min.	Max.	Unit
	Operating voltage	1.71	3.6	V
J1	SWD_CLK frequency of operation <ul style="list-style-type: none"> Serial wire debug 	0	25	MHz
J2	SWD_CLK cycle period	1/J1	—	ns
J3	SWD_CLK clock pulse width <ul style="list-style-type: none"> Serial wire debug 	20	—	ns
J4	SWD_CLK rise and fall times	—	3	ns
J9	SWD_DIO input data setup time to SWD_CLK rise	10	—	ns
J10	SWD_DIO input data hold time after SWD_CLK rise	0	—	ns
J11	SWD_CLK high to SWD_DIO data valid	—	32	ns
J12	SWD_CLK high to SWD_DIO high-Z	5	—	ns

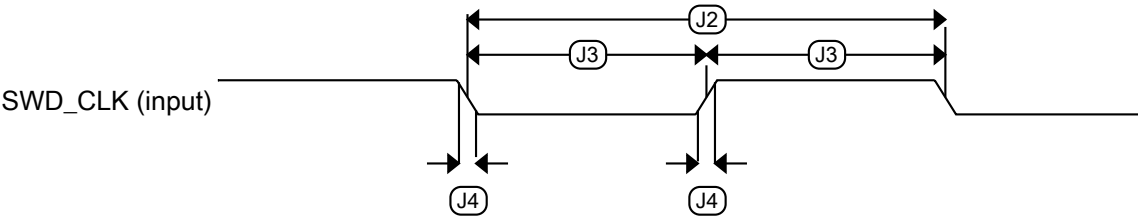


Figure 4. Serial wire clock input timing

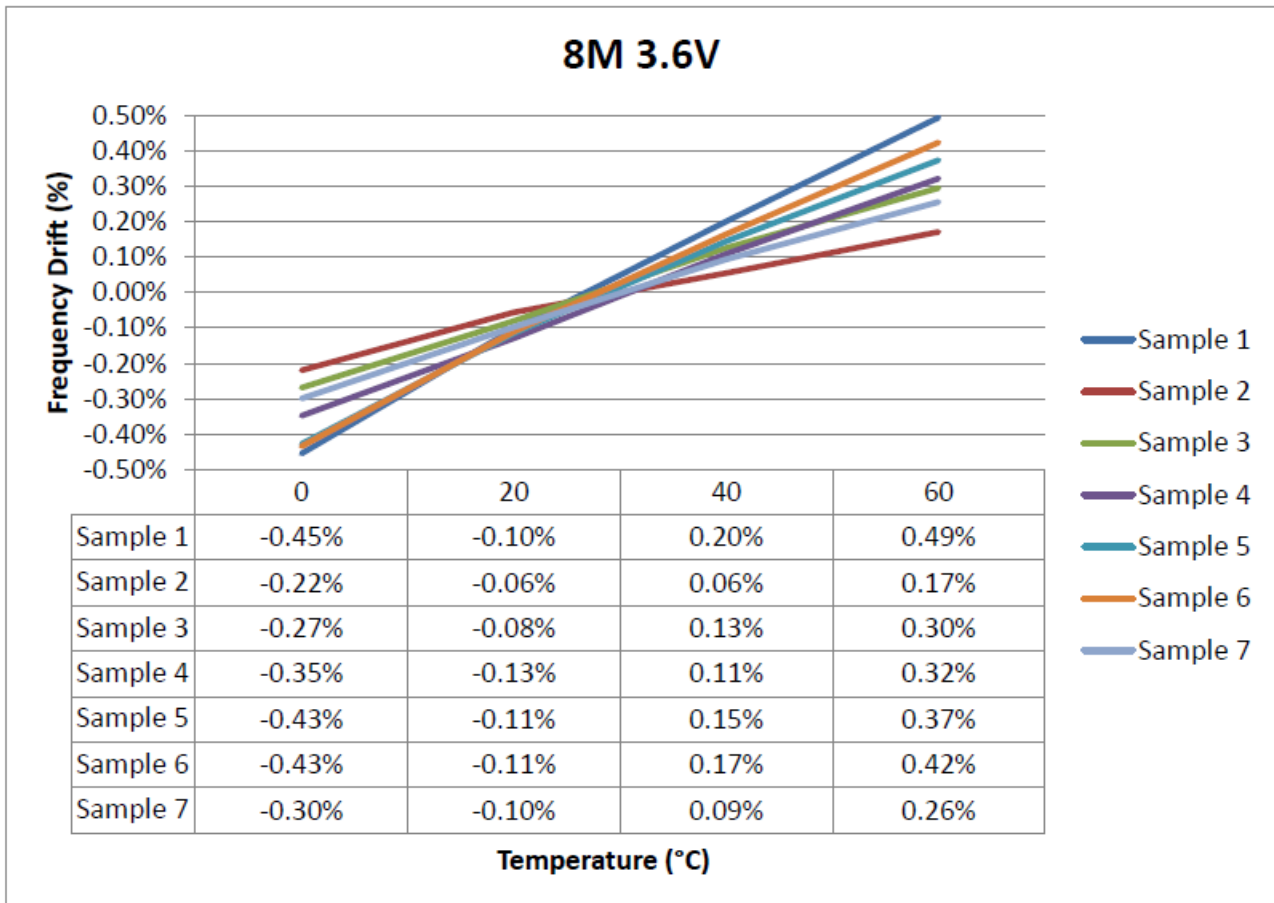


Figure 6. IRC8M Frequency Drift vs Temperature curve

3.3.2 Oscillator electrical specifications

3.3.2.1 Oscillator DC electrical specifications

Table 20. Oscillator DC electrical specifications

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
V _{DD}	Supply voltage	1.71	—	3.6	V	
I _{DDOSC}	Supply current — low-power mode (HGO=0)					1
	• 32 kHz	—	500	—	nA	
	• 4 MHz	—	200	—	μA	
	• 8 MHz (RANGE=01)	—	300	—	μA	
	• 16 MHz	—	950	—	μA	
		—	1.2	—	mA	

Table continues on the next page...

Table 20. Oscillator DC electrical specifications (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
	<ul style="list-style-type: none"> 24 MHz 32 MHz 	—	1.5	—	mA	
I _{DDOSC}	Supply current — high gain mode (HGO=1) <ul style="list-style-type: none"> 32 kHz 4 MHz 8 MHz (RANGE=01) 16 MHz 24 MHz 32 MHz 	—	25 400 500 2.5 3 4	—	μA μA μA mA mA mA	1
C _x	EXTAL load capacitance	—	—	—		2, 3
C _y	XTAL load capacitance	—	—	—		2, 3
R _F	Feedback resistor — low-frequency, low-power mode (HGO=0)	—	—	—	MΩ	2, 4
	Feedback resistor — low-frequency, high-gain mode (HGO=1)	—	10	—	MΩ	
	Feedback resistor — high-frequency, low-power mode (HGO=0)	—	—	—	MΩ	
	Feedback resistor — high-frequency, high-gain mode (HGO=1)	—	1	—	MΩ	
R _S	Series resistor — low-frequency, low-power mode (HGO=0)	—	—	—	kΩ	
	Series resistor — low-frequency, high-gain mode (HGO=1)	—	200	—	kΩ	
	Series resistor — high-frequency, low-power mode (HGO=0)	—	—	—	kΩ	
	Series resistor — high-frequency, high-gain mode (HGO=1)	—	0	—	kΩ	
V _{pp} ⁵	Peak-to-peak amplitude of oscillation (oscillator mode) — low-frequency, low-power mode (HGO=0)	—	0.6	—	V	
	Peak-to-peak amplitude of oscillation (oscillator mode) — low-frequency, high-gain mode (HGO=1)	—	V _{DD}	—	V	
	Peak-to-peak amplitude of oscillation (oscillator mode) — high-frequency, low-power mode (HGO=0)	—	0.6	—	V	
	Peak-to-peak amplitude of oscillation (oscillator mode) — high-frequency, high-gain mode (HGO=1)	—	V _{DD}	—	V	

1. V_{DD}=3.3 V, Temperature =25 °C

2. See crystal or resonator manufacturer's recommendation

3.4.1.1 Flash timing specifications — program and erase

The following specifications represent the amount of time the internal charge pumps are active and do not include command overhead.

Table 22. NVM program/erase timing specifications

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
$t_{hvp\text{gm}4}$	Longword Program high-voltage time	—	7.5	18	μs	—
$t_{hversscr}$	Sector Erase high-voltage time	—	13	113	ms	1
$t_{hversblk128k}$	Erase Block high-voltage time for 128 KB	—	52	452	ms	1

1. Maximum time based on expectations at cycling end-of-life.

3.4.1.2 Flash timing specifications — commands

Table 23. Flash command timing specifications

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
$t_{rd1blk128k}$	Read 1s Block execution time • 128 KB program flash	—	—	1.7	ms	1
$t_{rd1sec1k}$	Read 1s Section execution time (flash sector)	—	—	60	μs	1
t_{pgmchk}	Program Check execution time	—	—	45	μs	1
t_{rdrsr}	Read Resource execution time	—	—	30	μs	1
t_{pgm4}	Program Longword execution time	—	65	145	μs	—
$t_{ersblk128k}$	Erase Flash Block execution time • 128 KB program flash	—	88	600	ms	2
t_{ersscr}	Erase Flash Sector execution time	—	14	114	ms	2
t_{rd1all}	Read 1s All Blocks execution time	—	—	1.8	ms	1
t_{rdonce}	Read Once execution time	—	—	25	μs	1
$t_{pgmonce}$	Program Once execution time	—	65	—	μs	—
t_{ersall}	Erase All Blocks execution time	—	175	1300	ms	2
t_{vfykey}	Verify Backdoor Access Key execution time	—	—	30	μs	1
$t_{ersallu}$	Erase All Blocks Unsecure execution time	—	175	1300	ms	2

1. Assumes 25 MHz flash clock frequency.
2. Maximum times for erase parameters based on expectations at cycling end-of-life.

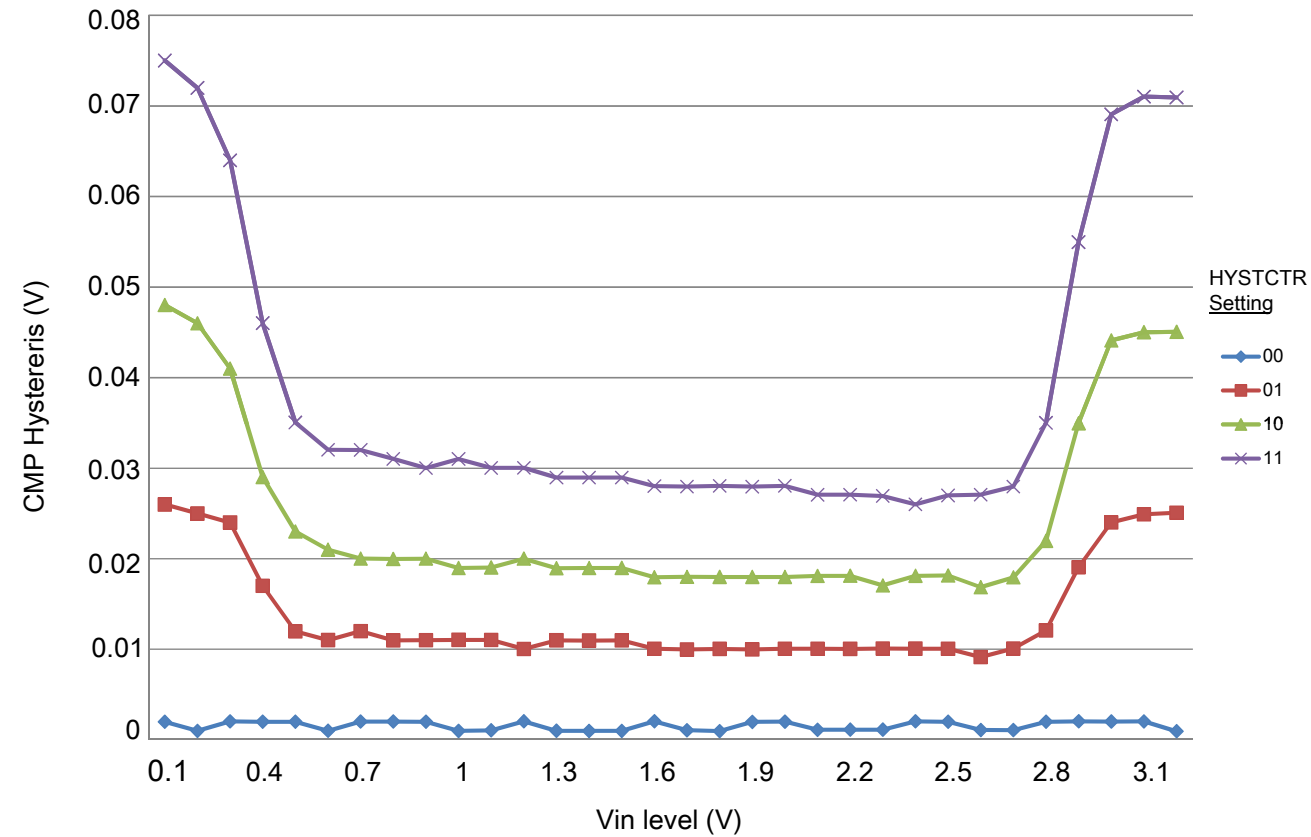


Figure 10. Typical hysteresis vs. Vin level (VDD = 3.3 V, PMODE = 0)

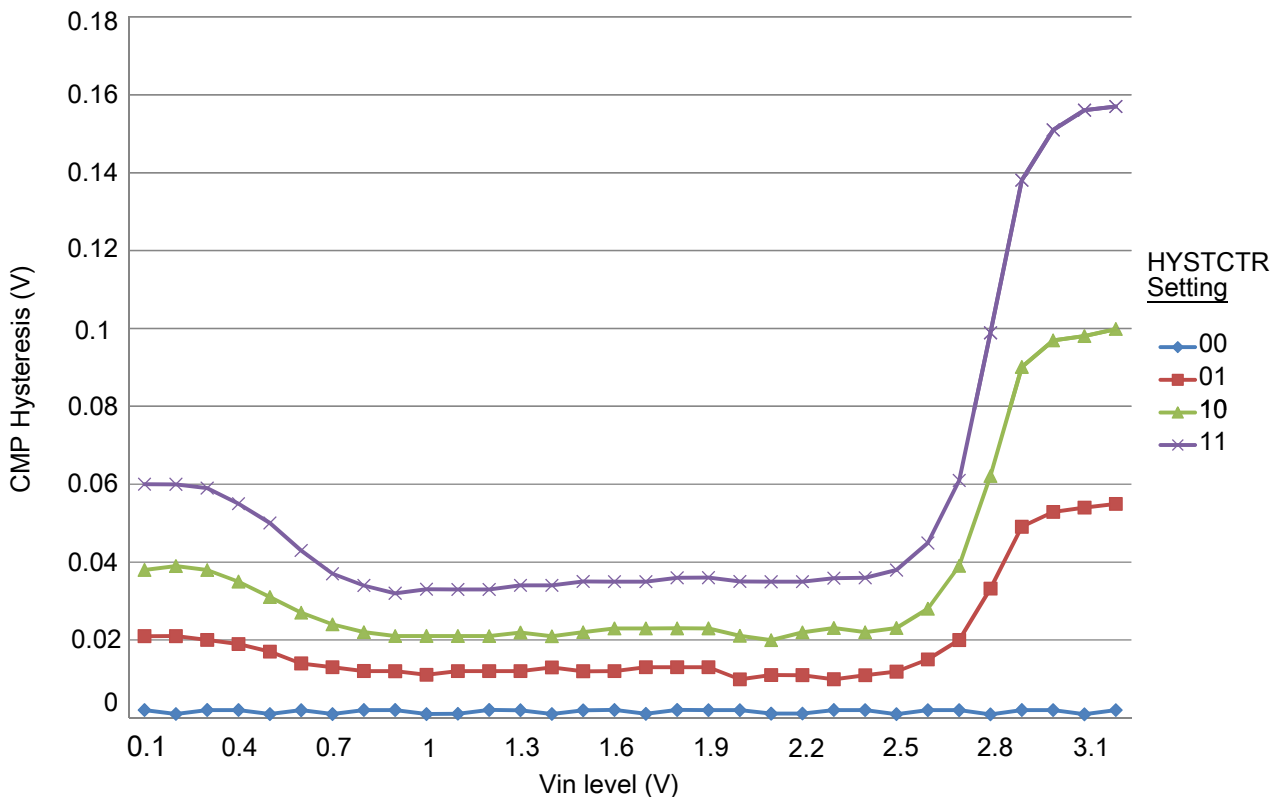


Figure 11. Typical hysteresis vs. Vin level (VDD = 3.3 V, PMODE = 1)

3.6.4 12-bit DAC electrical characteristics

3.6.4.1 12-bit DAC operating requirements

Table 33. 12-bit DAC operating requirements

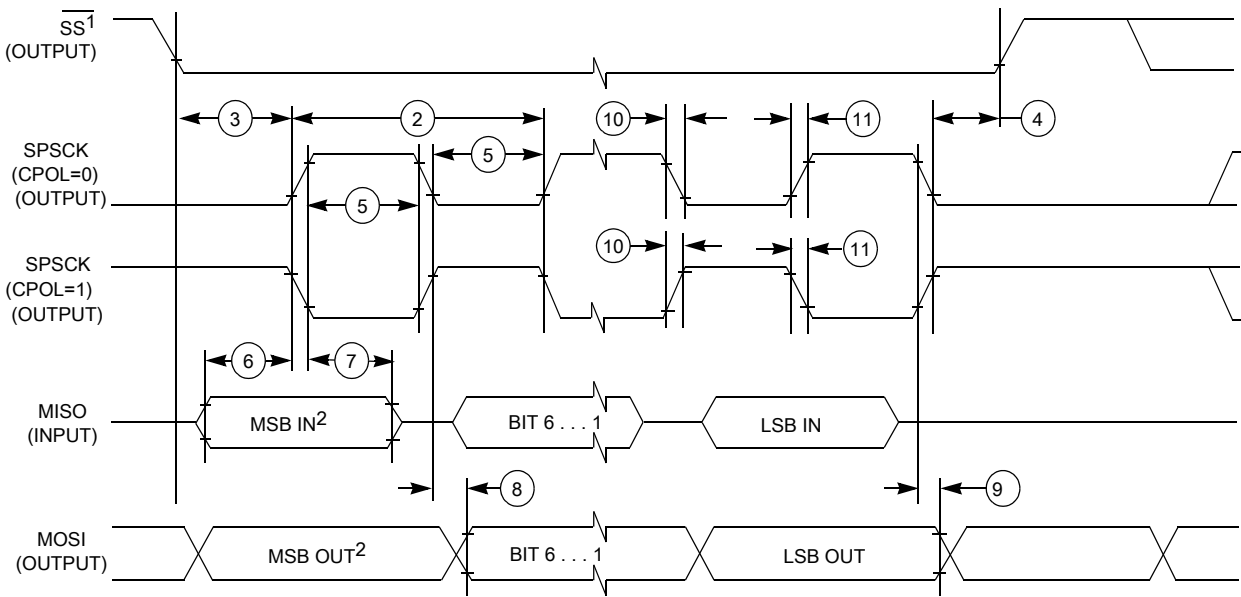
Symbol	Description	Min.	Max.	Unit	Notes
V_{DDA}	Supply voltage		3.6	V	
V_{DACR}	Reference voltage	1.13	3.6	V	1
C_L	Output load capacitance	—	100	pF	2
I_L	Output load current	—	1	mA	

1. The DAC reference can be selected to be V_{DDA} or V_{REFH} .
2. A small load capacitance (47 pF) can improve the bandwidth performance of the DAC.

Table 37. SPI master mode timing on slew rate enabled pads (continued)

Num.	Symbol	Description	Min.	Max.	Unit	Note
8	t_v	Data valid (after SPSCCK edge)	—	52	ns	—
9	t_{HO}	Data hold time (outputs)	0	—	ns	—
10	t_{RI}	Rise time input	—	$t_{periph} - 25$	ns	—
	t_{FI}	Fall time input				
11	t_{RO}	Rise time output	—	36	ns	—
	t_{FO}	Fall time output				

1. For SPI0 f_{periph} is the bus clock (f_{BUS}). For SPI1 f_{periph} is the system clock (f_{SYS}).
2. $t_{periph} = 1/f_{periph}$

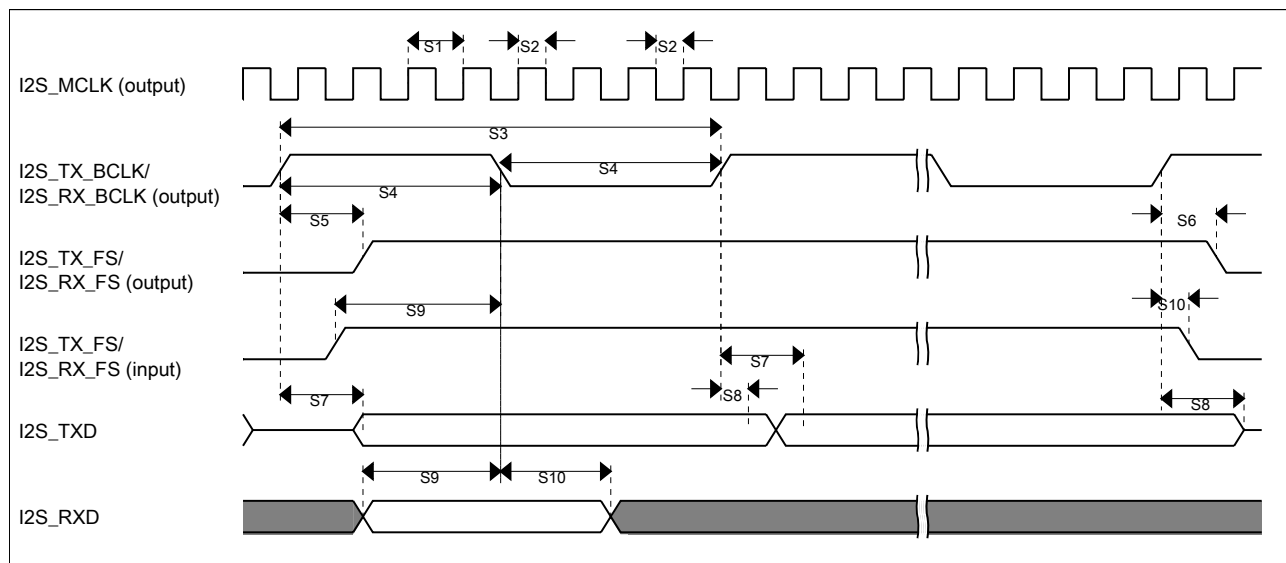


1. If configured as an output.
2. LSBF = 0. For LSBF = 1, bit order is LSB, bit 1, ..., bit 6, MSB.

Figure 14. SPI master mode timing (CPHA = 0)

Table 42. I2S/SAI master mode timing (continued)

Num.	Characteristic	Min.	Max.	Unit
S6	I2S_TX_BCLK/I2S_RX_BCLK to I2S_TX_FS/ I2S_RX_FS output invalid	0	—	ns
S7	I2S_TX_BCLK to I2S_TXD valid	—	19	ns
S8	I2S_TX_BCLK to I2S_TXD invalid	0	—	ns
S9	I2S_RXD/I2S_RX_FS input setup before I2S_RX_BCLK	26	—	ns
S10	I2S_RXD/I2S_RX_FS input hold after I2S_RX_BCLK	0	—	ns


Figure 19. I2S/SAI timing — master modes
Table 43. I2S/SAI slave mode timing

Num.	Characteristic	Min.	Max.	Unit
	Operating voltage	1.71	3.6	V
S11	I2S_TX_BCLK/I2S_RX_BCLK cycle time (input)	80	—	ns
S12	I2S_TX_BCLK/I2S_RX_BCLK pulse width high/low (input)	45%	55%	MCLK period
S13	I2S_TX_FS/I2S_RX_FS input setup before I2S_TX_BCLK/I2S_RX_BCLK	10	—	ns
S14	I2S_TX_FS/I2S_RX_FS input hold after I2S_TX_BCLK/I2S_RX_BCLK	2	—	ns
S15	I2S_TX_BCLK to I2S_TXD/I2S_TX_FS output valid	—	33	ns
S16	I2S_TX_BCLK to I2S_TXD/I2S_TX_FS output invalid	0	—	ns
S17	I2S_RXD setup before I2S_RX_BCLK	10	—	ns

Table continues on the next page...

Table 44. I2S/SAI master mode timing in VLPR, VLPW, and VLPS modes (full voltage range) (continued)

Num.	Characteristic	Min.	Max.	Unit
S8	I2S_TX_BCLK to I2S_TXD invalid	0	—	ns
S9	I2S_RXD/I2S_RX_FS input setup before I2S_RX_BCLK		—	ns
S10	I2S_RXD/I2S_RX_FS input hold after I2S_RX_BCLK	0	—	ns

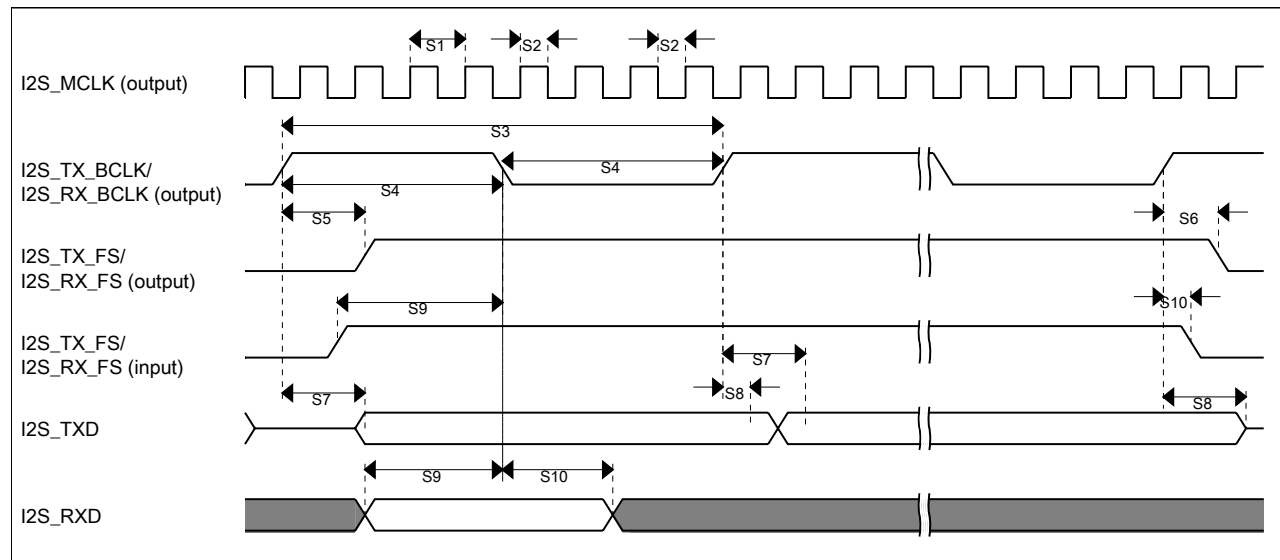


Figure 21. I2S/SAI timing — master modes

Table 45. I2S/SAI slave mode timing in VLPR, VLPW, and VLPS modes (full voltage range)

Num.	Characteristic	Min.	Max.	Unit
	Operating voltage	1.71	3.6	V
S11	I2S_TX_BCLK/I2S_RX_BCLK cycle time (input)	250	—	ns
S12	I2S_TX_BCLK/I2S_RX_BCLK pulse width high/low (input)	45%	55%	MCLK period
S13	I2S_TX_FS/I2S_RX_FS input setup before I2S_TX_BCLK/I2S_RX_BCLK	30	—	ns
S14	I2S_TX_FS/I2S_RX_FS input hold after I2S_TX_BCLK/I2S_RX_BCLK	2	—	ns
S15	I2S_TX_BCLK to I2S_TXD/I2S_TX_FS output valid	—	87	ns
S16	I2S_TX_BCLK to I2S_TXD/I2S_TX_FS output invalid	0	—	ns
S17	I2S_RXD setup before I2S_RX_BCLK	30	—	ns
S18	I2S_RXD hold after I2S_RX_BCLK	2	—	ns
S19	I2S_TX_FS input assertion to I2S_TXD output valid ¹	—	72	ns

5 Pinouts and Packaging

5.1 KL27 Signal Multiplexing and Pin Assignments

The following table shows the signals available on each pin and the locations of these pins on the devices supported by this document. The Port Control Module is responsible for selecting which ALT functionality is available on each pin.

NOTE

VREFH can act as VREF_OUT when VREFV1 module is enabled.

NOTE

It is prohibited to set VREFEN in 32 QFN pin package as 1.2 V on-chip voltage is not available in this package.

32 QFN	48 QFN	64 MAP BGA	64 LQFP	Pin Name	Default	ALT0	ALT1	ALT2	ALT3	ALT4	ALT5	ALT6	ALT7
—	—	B1	2	PTE1	DISABLED		PTE1	SPI1_MOSI	LPUART1_RX		SPI1_MISO	I2C1_SCL	
—	1	—	3	VDD	VDD	VDD							
—	7	G1	9	PTE20	ADC0_DP0/ ADC0_SE0	ADC0_DP0/ ADC0_SE0	PTE20		TPM1_CH0	LPUART0_TX		FXIO0_D4	
—	8	F1	10	PTE21	ADC0_DM0/ ADC0_SE4a	ADC0_DM0/ ADC0_SE4a	PTE21		TPM1_CH1	LPUART0_RX		FXIO0_D5	
—	—	G2	11	PTE22	ADC0_DP3/ ADC0_SE3	ADC0_DP3/ ADC0_SE3	PTE22		TPM2_CH0	UART2_TX		FXIO0_D6	
—	—	F2	12	PTE23	ADC0_DM3/ ADC0_SE7a	ADC0_DM3/ ADC0_SE7a	PTE23		TPM2_CH1	UART2_RX		FXIO0_D7	
—	10	G4	14	VREFH	VREFH	VREFH							
—	11	G3	15	VREFL	VREFL	VREFL							
—	13	H1	17	PTE29	CMP0_IN5/ ADC0_SE4b	CMP0_IN5/ ADC0_SE4b	PTE29		TPM0_CH2	TPM_CLKIN0			
—	—	H3	19	PTE31	DISABLED		PTE31		TPM0_CH4				
—	15	H4	20	PTE24	DISABLED		PTE24		TPM0_CH0		I2C0_SCL		
—	16	H5	21	PTE25	DISABLED		PTE25		TPM0_CH1		I2C0_SDA		
—	—	F5	27	PTA5	DISABLED		PTA5	USB_CLKIN	TPM0_CH2			I2S0_TX_BCLK	
—	—	H6	28	PTA12	DISABLED		PTA12		TPM1_CH0			I2S0_TXD0	
—	—	G6	29	PTA13	DISABLED		PTA13		TPM1_CH1			I2S0_TX_FS	
—	29	E7	37	PTB2	ADC0_SE12	ADC0_SE12	PTB2	I2C0_SCL	TPM2_CH0				
—	30	E8	38	PTB3	ADC0_SE13	ADC0_SE13	PTB3	I2C0_SDA	TPM2_CH1				

Pinouts and Packaging

32 QFN	48 QFN	64 MAP BGA	64 LQFP	Pin Name	Default	ALT0	ALT1	ALT2	ALT3	ALT4	ALT5	ALT6	ALT7
—	31	E6	39	PTB16	DISABLED		PTB16	SPI1_MOSI	LPUART0_RX	TPM_CLKIN0	SPI1_MISO		
—	32	D7	40	PTB17	DISABLED		PTB17	SPI1_MISO	LPUART0_TX	TPM_CLKIN1	SPI1_MOSI		
—	—	D6	41	PTB18	DISABLED		PTB18		TPM2_CH0	I2S0_TX_BCLK			
—	—	C7	42	PTB19	DISABLED		PTB19		TPM2_CH1	I2S0_TX_FS			
—	33	D8	43	PTC0	ADC0_SE14	ADC0_SE14	PTC0		EXTRG_IN	audioUSB_SOF_OUT	CMP0_OUT	I2S0_TXD0	
—	—	E3	47	VSS	VSS	VSS							
—	—	E4	48	VDD	VDD	VDD							
—	—	A6	53	PTC8	CMP0_IN2	CMP0_IN2	PTC8	I2C0_SCL	TPM0_CH4	I2S0_MCLK			
—	—	B5	54	PTC9	CMP0_IN3	CMP0_IN3	PTC9	I2C0_SDA	TPM0_CH5	I2S0_RX_BCLK			
—	—	B4	55	PTC10	DISABLED		PTC10	I2C1_SCL		I2S0_RX_FS			
—	—	A5	56	PTC11	DISABLED		PTC11	I2C1_SDA		I2S0_RXD0			
—	41	C3	57	PTD0	DISABLED		PTD0	SPI0_SS		TPM0_CH0		FXIO0_D0	
—	42	A4	58	PTD1	ADC0_SE5b	ADC0_SE5b	PTD1	SPI0_SCK		TPM0_CH1		FXIO0_D1	
—	43	C2	59	PTD2	DISABLED		PTD2	SPI0_MOSI	UART2_RX	TPM0_CH2	SPI0_MISO	FXIO0_D2	
—	44	B3	60	PTD3	DISABLED		PTD3	SPI0_MISO	UART2_TX	TPM0_CH3	SPI0_MOSI	FXIO0_D3	
—	—	C5	—	NC	NC	NC							
1	—	A1	1	PTE0	DISABLED		PTE0/CLKOUT32K	SPI1_MISO	LPUART1_TX	RTC_CLKOUT	CMP0_OUT	I2C1_SDA	
2	2	C4	4	VSS	VSS	VSS							
3	3	E1	5	USB0_DP	USB0_DP	USB0_DP							
4	4	D1	6	USB0_DM	USB0_DM	USB0_DM							
5	5	E2	7	VOUT33	VOUT33	VOUT33							
6	6	D2	8	VREGIN	VREGIN	VREGIN							
7	9	F4	13	VDDA	VDDA	VDDA							
8	12	F3	16	VSSA	VSSA	VSSA							
9	14	H2	18	PTE30	DAC0_OUT/ ADC0_SE23/ CMP0_IN4	DAC0_OUT/ ADC0_SE23/ CMP0_IN4	PTE30		TPM0_CH3	TPM_CLKIN1	LPUART1_TX	LPTMR0_ALT1	
10	17	D3	22	PTA0	SWD_CLK		PTA0		TPM0_CH5				SWD_CLK
11	18	D4	23	PTA1	DISABLED		PTA1	LPUART0_RX	TPM2_CH0				
12	19	E5	24	PTA2	DISABLED		PTA2	LPUART0_TX	TPM2_CH1				
13	20	D5	25	PTA3	SWD_DIO		PTA3	I2C1_SCL	TPM0_CH0				SWD_DIO
14	21	G5	26	PTA4	NMI_b		PTA4	I2C1_SDA	TPM0_CH1				NMI_b
15	22	G7	30	VDD	VDD	VDD							
16	23	H7	31	VSS	VSS	VSS							

7.1 Description

Part numbers for the chip have fields that identify the specific part. You can use the values of these fields to determine the specific part you have received.

7.2 Format

Part numbers for this device have the following format:

Q KL## A FFF R T PP CC N

7.3 Fields

This table lists the possible values for each field in the part number (not all combinations are valid):

Table 46. Part number fields descriptions

Field	Description	Values
Q	Qualification status	<ul style="list-style-type: none"> M = Fully qualified, general market flow P = Prequalification
KL##	Kinetis family	<ul style="list-style-type: none"> KL27
A	Key attribute	<ul style="list-style-type: none"> Z = Cortex-M0+
FFF	Program flash memory size	
R	Silicon revision	<ul style="list-style-type: none"> (Blank) = Main A = Revision after main
T	Temperature range (°C)	<ul style="list-style-type: none"> V = -40 to 105
PP	Package identifier	<ul style="list-style-type: none"> FM = 32 QFN (5 mm x 5 mm) FT = 48 QFN (7 mm x 7 mm) LH = 64 LQFP (10 mm x 10 mm) MP = 64 MAPBGA (5 mm x 5 mm)
CC	Maximum CPU frequency (MHz)	<ul style="list-style-type: none"> 4 = 48 MHz
N	Packaging type	<ul style="list-style-type: none"> R = Tape and reel

7.4 Example

This is an example part number:

MKL27Z256VFT4

8 Terminology and guidelines

8.1 Definitions

Key terms are defined in the following table:

Term	Definition
Rating	<p>A minimum or maximum value of a technical characteristic that, if exceeded, may cause permanent chip failure:</p> <ul style="list-style-type: none"> • <i>Operating ratings</i> apply during operation of the chip. • <i>Handling ratings</i> apply when the chip is not powered. <p>NOTE: The likelihood of permanent chip failure increases rapidly as soon as a characteristic begins to exceed one of its operating ratings.</p>
Operating requirement	A specified value or range of values for a technical characteristic that you must guarantee during operation to avoid incorrect operation and possibly decreasing the useful life of the chip
Operating behavior	A specified value or range of values for a technical characteristic that are guaranteed during operation if you meet the operating requirements and any other specified conditions
Typical value	<p>A specified value for a technical characteristic that:</p> <ul style="list-style-type: none"> • Lies within the range of values specified by the operating behavior • Is representative of that characteristic during operation when you meet the typical-value conditions or other specified conditions <p>NOTE: Typical values are provided as design guidelines and are neither tested nor guaranteed.</p>

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